

Form 1449*	Atty. Docket No.: 303.324US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
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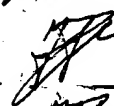
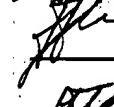
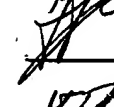
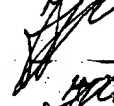
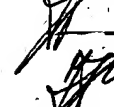
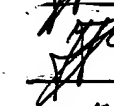



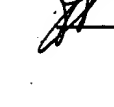

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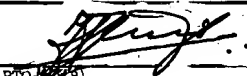
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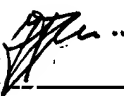
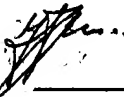
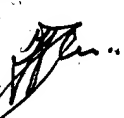
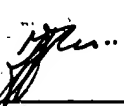
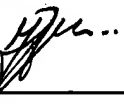
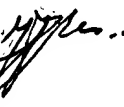
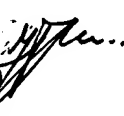
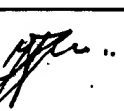
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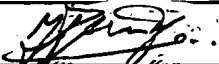
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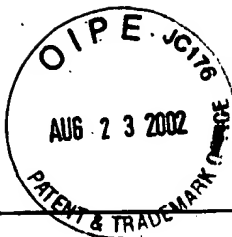
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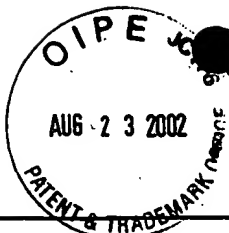
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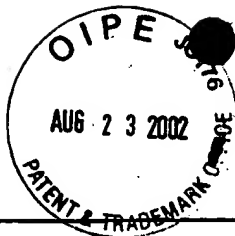
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Sheet 8 of 10

Form 1449*

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Atty. Docket No.: 303.324US4

Serial No. Unknown

Applicant: Leonard Forbes et al.

Filing Date: Herewith

Gross: Unknown

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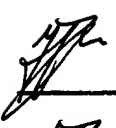
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Form 1449*	Atty. Docket No.: 303.324US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
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Form 1449*	Atty. Docket No.: 303.324US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown

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First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Unknown

Attorney Docket No: 00303.324US4

Sheet 1 of 1

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